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AMENDMENTS TO THE ABSTRACT OF THE SPECIFICATION

MAR 30 2007

- Please replace paragraph entitled ABSTRACT OF THE DICLOSURE with the following amended paragraph:

ABSTRACT OF THE DISCLOSURE

The present invention provides a [A] deposition process for plasma enhanced chemical vapor deposition of a coating on a substrate. The process comprises determining a target process condition within a chamber of an expanding thermal plasma generator for plasma enhanced chemical vapor deposition of a coating on a substrate; the generator comprising a cathode, a replaceable cascade plate and an anode comprising a [with] concentric orifice; and thereafter replacing the cascade plate with another plate having a configured orifice to effect the identified target process condition. [;] The and generating a plasma is then generated at the target process condition by providing a plasma gas to the plasma generator and ionizing the plasma gas in an arc between cathode and anode within the generator and expanding the gas as a plasma onto a substrate in a deposition chamber A deposition apparatus for generating a controllable plasma; comprises a deposition chamber; adapted to be maintained at subatmospheric pressure; an article support within the deposition chamber; an expanding thermal plasma generator comprising a cathode, a single cascade plate and an anode and a communicating orifice through the cascade plate, the orifice having a length of 1 mm to less than 20 mm.